PCN Number: 20			5071	.5001			P	CN Date:	07/15/2016
Title:	Qualification of F	RFAB for Select C05 Devices							
Customer Contact:			PCN Manager Dept			t:	Quality Services		
Proposed 1 st Ship Date:		10/15/2016 Estimated Sample Availability:		ple	е		e provided at ple request.		
Change Type:									
Assem	nbly Site			Assembly Process			Assembly Materials		
Design				Electrical Specification			Mechanical Specification		
Test Site				Packing/Shipping/Labeling			Test Process		
Wafer Bump Site				Wafer Bump Material			Wafer Bump Process		
				Wafer Fab Materials			Wafer Fab Process		
				Part number	r change				
PCN Details									
Description of Change:									

Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional wafer Fab source for the selected devices listed in "Product Affected" section.

	Current Site			Additional Site	9
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
DP1DM5	C05	200 mm	RFAB	C05	300 mm

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

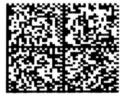
Changes to product identification resulting from this PCN:

Current

Chip Site	(20L)	Code (21L)	Chip Site City
CI : C''	Chip Site Origin Code	Chip Site Country	Chip Site City
New			
DP1DM5	DM5	USA	Dallas
Chip Sites	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City

Sample product shipping label (not actual product label)





(1P) SN74LS07NSR (D) 0336 31T)LOT: 3959047MLA 4W) TKY(1T) 7523483S12 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

TLV320ADC3101IRGER TLV320ADC3101IRGET

Qualification Report

TLV320ADC3101IRGE in RFAB (DMOS5 TO RFAB OFFLOAD - C05, Die: G2TIADC3101C) Approve Date 15-Jul-2016

Product Attributes

Attributes	Qual Device: TLV320ADC3101IRGER	QBS Process Reference: ADS58C48IPFPR (QFP)	QBS Process Reference: VSP6825BZRC
Assembly Site	CLARK-AT	-	PHI
Package Family	QFN	HTQFP	JRBGA
Wafer Fab Supplier	RFAB	RFAB	HIJI, RFAB
Wafer Fab Process	1833C05	1833C05	1833C05, LBC4

⁻ QBS: Qual by Similarity

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

	Туре	Test Name / Condition	Duration	Qual Device: TLV320ADC3101IRGER	QBS Process Reference: ADS58C48IPFPR (QFP)	QBS Process Reference: VSP6825BZRC
	AC	Autoclave 121C	96 Hours	-	3/231/0	-
	ED	Electrical Characterization	Per Datasheet Parameters	Pass	-	-
	HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	3/230/0
	HTOL	Life Test, 125C	1000 Hours	-	2/152/0	-
	HTOL	Life Test, 140C	480 Hours	-	-	3/231/0
	HTSL	High Temp Storage Bake 170C	420 Hours	-	-	3/231/0
	TC	Temperature Cycle, - 65/150C	500 Cycles	-	3/231/0	3/231/0
	WBP	Bond Pull	Wires	1/76/0	-	-
Γ	WBS	Ball Bond Shear	Wires	1/76/0	-	-

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com

⁻ Qual Device TLV320ADC3101 IRGER is qualified at LEVEL2-260C